

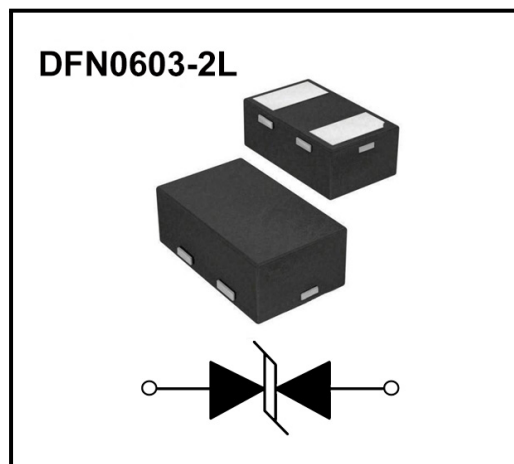
BNDY2L5A0C0L1

ESD Protection Diode

Features

- 45Watts peak pulse power ($t_p = 8/20\mu s$)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping Voltage
- Low leakage current
- Low capacitance ($C_j = 3.5pF$ typ.)
- Protection one data/power line
- IEC 61000-4-2 $\pm 25kV$ contact ; $\pm 25kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 3.0A (8/20 μs)

Package



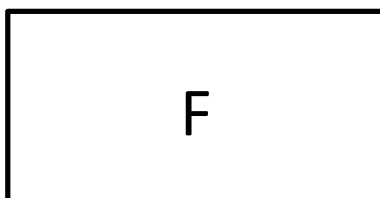
Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation

Mechanical Characteristics

- DFN0603-2L package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Marking



Ordering information

Order code	Package	Base qty	Delivery mode
BNDY2L5A0C0L1	DFN0603-2L	10k	Tape and reel

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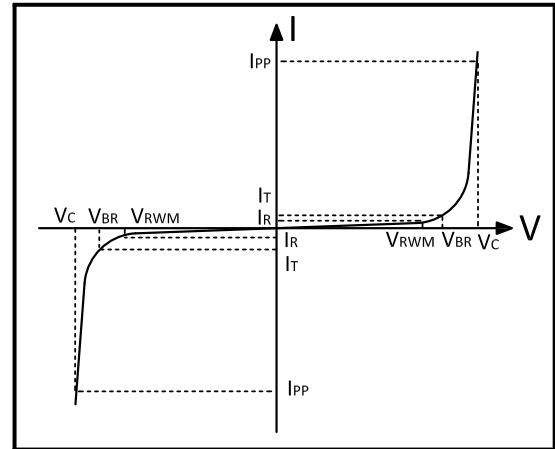


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ESD Protection Diode

Electrical Parameters ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note: 8/20us pulse Waveform.

Absolute Maximum Rating

Rating	Symler	Value	Units
Peak Pulse Power ($t_p = 8/20\mu\text{s}$)	P_{PP}	45	Watts
Peak Pulse Current ($t_p = 8/20\mu\text{s}$)	I_{PP}	3.0	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	25	KV
ESD per IEC 61000-4-2 (Contact)		25	
Lead Soldering Temperature	T_L	260(10seconds)	$^\circ\text{C}$
Junction Temperature	T_J	-55 to + 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 150	$^\circ\text{C}$

Electrical Characteristics

Parameter	Symler	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}	—	—	—	5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	6.0	7.0	9.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5\text{V}, T = 25^\circ\text{C}$	—	0.1	0.5	μA
Peak Pulse Current	I_{PP}	$t_p = 8/20\mu\text{s}$	—	—	3.0	A
Clamping Voltage	V_C	$I_{PP} = 3.0\text{A}, t_p = 8/20\mu\text{s}$	—	—	11	V
Junction Capacitance	C_j	$V_R = 0\text{V}, T = 25^\circ\text{C}, f = 1\text{MHz}$	—	3.5	4.5	pF



Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

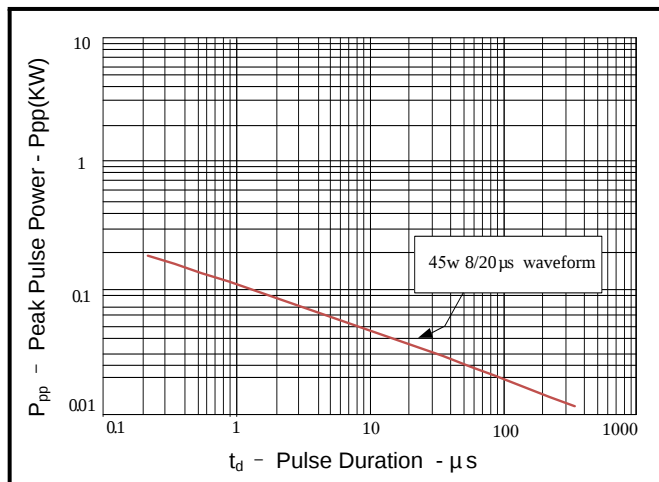


Figure 2: Power Derating Curve

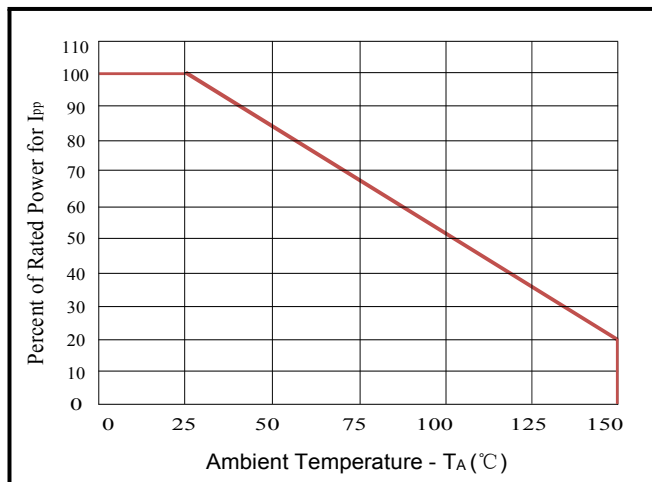


Figure 3: Pulse Waveform

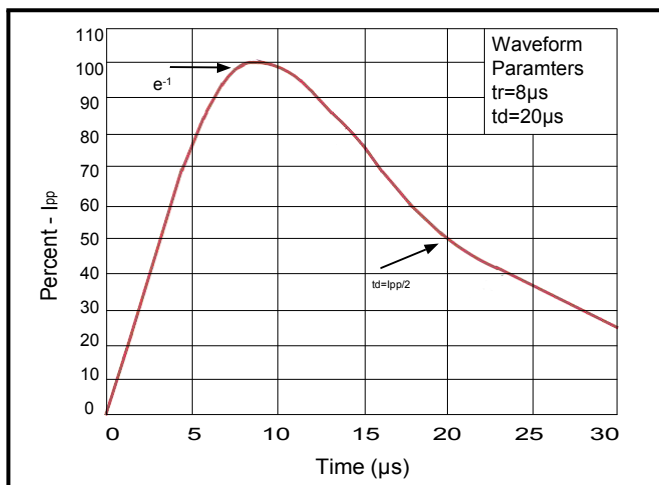
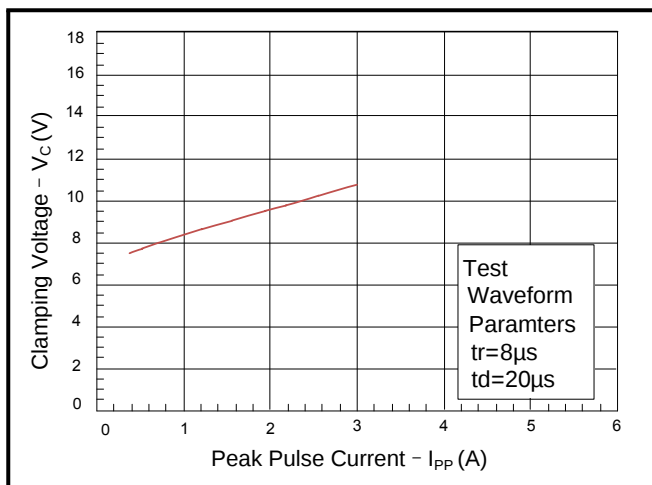
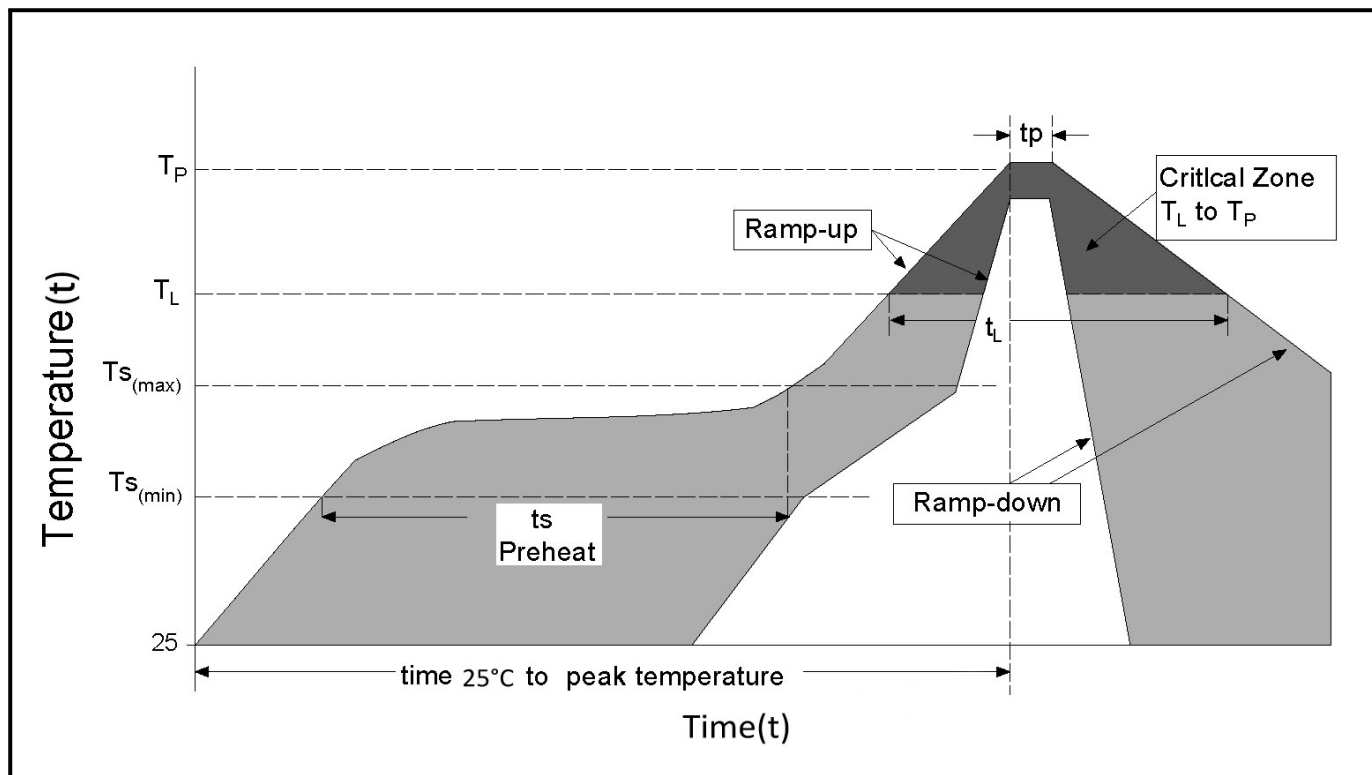


Figure 4: Clamping Voltage vs. Ipp



Soldering Parameters



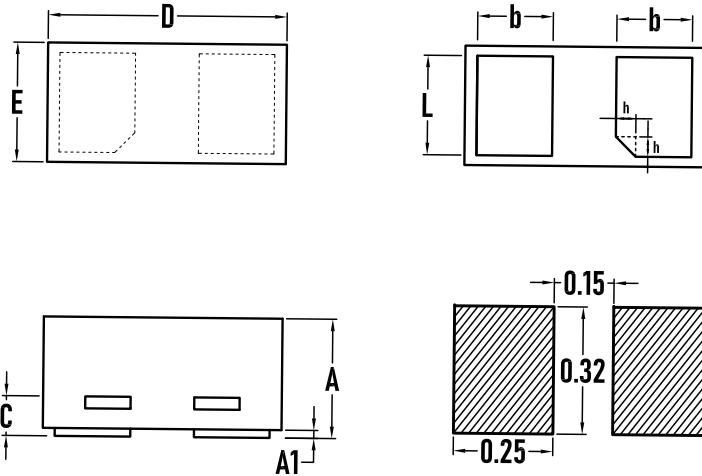
Reflow Condition		Lead-free assembly
Pre Heat	- Temperature Min ($T_{S(min)}$)	150°C
	- Temperature Max ($T_{S(max)}$)	200°C
	- Time (min to max) (t_s)	60 - 180 secs
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/second max
$T_{S(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Time (t_L)	60 - 150 secs
Peak Temperature (T_P)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 - 40 secs
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (t)		8 minutes Max.
Do not exceed		260°C



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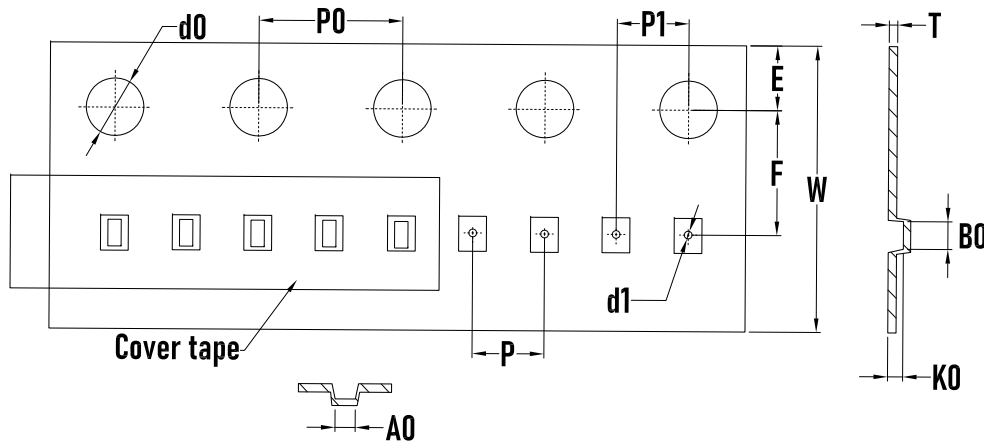
ESD Protection Diode

Outline Drawing – DFN0603-2L



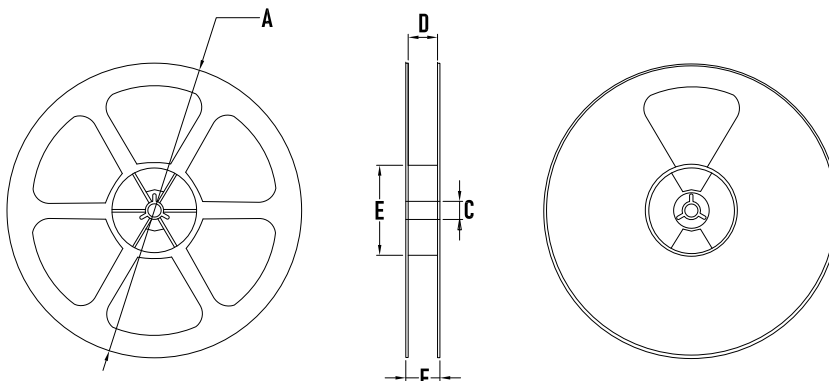
SYMBOL	MILLIMETER		
	MIN.	Typ.	MAX.
A	0.28	0.30	0.32
A1	0.00	0.02	0.05
C	0.05	0.10	0.15
D	0.55	0.60	0.65
E	0.25	0.30	0.35
b	0.14	0.19	0.24
L	0.20	0.25	0.30
h	—	0.05	0.10

Packaging Tape - DFN0603-2L



SYMBOL	MILLIMETER
A0	0.39±0.03
B0	0.70±0.03
d0	1.55±0.05
d1	0.20±0.05
E	1.75±0.10
F	3.50±0.04
K0	0.37 ^{+0.03} _{-0.02}
P	2.00±0.10
P0	4.00±0.10
P1	2.00±0.05
W	8.00±0.10
T	0.18±0.03

Packaging Reel



SYMBOL	MILLIMETER
A	178±2
C	13.0 ^{+0.5} _{-0.2}
D	9.5
E	55±5
F	14.4 max.
Quantity	10000PCS

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